

| Ref # | Hits    | Search Query  | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|---------|---|---|------------------|---------|------------------|
| L1    | 3008070 | memory or storage   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/01/18 12:41 |
| L2    | 3910    | 1 and cell with bit with end  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/01/18 12:42 |
| L3    | 234     | 2 and read\$5 with drain near3<br>(voltage or potential or level)                                 | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/01/18 12:43 |
| L4    | 10      | 3 and verify near3 (program\$6 or<br>writ\$5) with drain near3 (voltage<br>or potential or level) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT | OR               | ON      | 2005/01/18 12:44 |